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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

Product Status	Active
Core Processor	STM8
Core Size	8-Bit
Speed	16MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	Infrared, POR, PWM, WDT
Number of I/O	18
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-UFQFN
Supplier Device Package	20-UFQFPN (3x3)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8l101f3u6tr

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

# Contents

1				
2	Desc	ription		
3	Prod	uct overview		
	3.1	Central processing unit STM811		
	3.2	Development tools		
	3.3	Single wire data interface (SWIM) and debug module		
	3.4	Interrupt controller		
	3.5	Memory		
	3.6	Low power modes		
	3.7	Voltage regulators		
	3.8	Clock control		
	3.9	Independent watchdog 12		
	3.10	Auto-wakeup counter 13		
	3.11	General purpose and basic timers		
	3.12	Beeper		
	3.13	Infrared (IR) interface		
	3.14	Comparators		
	3.15	USART		
	3.16	SPI 14		
	3.17	I <sup>2</sup> C 14		
4	Pin d	lescription		
5	Mem	ory and register map		
6	Inter	rupt vector mapping		
7	Optic	on bytes		
8	Uniq	ue ID		



13	<b>Revision history</b>		82
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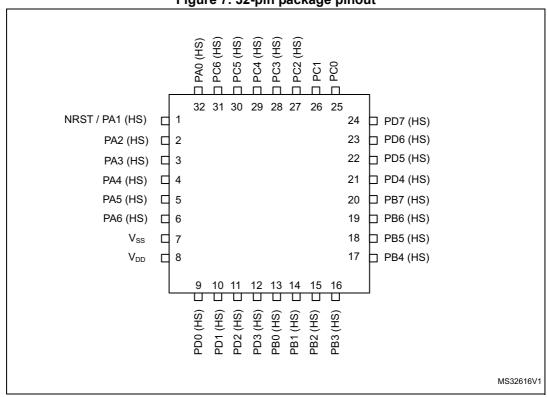


Figure 7. 32-pin package pinout

1. Example given for the UFQFPN32 package. The pinout is the same for the LQFP32 package.

2. HS corresponds to 20 mA high sink/source capability.

 High sink LED driver capability available on PA0. Refer to the description of the IR\_CR register in the STM8L reference manual (RM0013).



Table 7. General hardware register map (continued)					
Address	Block	Register label	Register name	Reset status	
0x00 5280		TIM3_CR1	TIM3 control register 1	0x00	
0x00 5281		TIM3_CR2	TIM3 control register 2	0x00	
0x00 5282		TIM3_SMCR	TIM3 slave mode control register	0x00	
0x00 5283		TIM3_ETR	TIM3 external trigger register	0x00	
0x00 5284		TIM3_IER	TIM3 interrupt enable register	0x00	
0x00 5285		TIM3_SR1	TIM3 status register 1	0x00	
0x00 5286		TIM3_SR2	TIM3 status register 2	0x00	
0x00 5287		TIM3_EGR	TIM3 event generation register	0x00	
0x00 5288		TIM3_CCMR1	TIM3 capture/compare mode register 1	0x00	
0x00 5289		TIM3_CCMR2	TIM3 capture/compare mode register 2	0x00	
0x00 528A	ТІМЗ	TIM3_CCER1	TIM3 capture/compare enable register 1	0x00	
0x00 528B	TIMO	TIM3_CNTRH	TIM3 counter high	0x00	
0x00 528C		TIM3_CNTRL	TIM3 counter low	0x00	
0x00 528D		TIM3_PSCR	TIM3 prescaler register	0x00	
0x00 528E		TIM3_ARRH	TIM3 auto-reload register high	0xFF	
0x00 528F		TIM3_ARRL	TIM3 auto-reload register low	0xFF	
0x00 5290		TIM3_CCR1H	TIM3 capture/compare register 1 high	0x00	
0x00 5291		TIM3_CCR1L	TIM3 capture/compare register 1 low	0x00	
0x00 5292		TIM3_CCR2H	TIM3 capture/compare register 2 high	0x00	
0x00 5293		TIM3_CCR2L	TIM3 capture/compare register 2 low	0x00	
0x00 5294		TIM3_BKR	TIM3 break register	0x00	
0x00 5295		TIM3_OISR	TIM3 output idle state register	0x00	
0x00 5296 to 0x00 52DF		F	Reserved area (74 bytes)		
0x00 52E0		TIM4_CR1	TIM4 control register 1	0x00	
0x00 52E1		TIM4_CR2	TIM4 control register 2	0x00	
0x00 52E2		TIM4_SMCR	TIM4 Slave mode control register	0x00	
0x00 52E3		TIM4_IER	TIM4 interrupt enable register	0x00	
0x00 52E4	TIM4	TIM4_SR1	TIM4 Status register 1	0x00	
0x00 52E5		TIM4_EGR	TIM4 event generation register	0x00	
0x00 52E6		TIM4_CNTR	TIM4 counter	0x00	
0x00 52E7		TIM4_PSCR	TIM4 prescaler register	0x00	
0x00 52E8		TIM4_ARR	TIM4 auto-reload register low	0xFF	

 Table 7. General hardware register map (continued)



IRQ No.	Source block	Description	Wakeup from Halt mode	Wakeup from Active-halt mode	Wakeup from Wait (WFI mode)	Wakeup from Wait (WFE mode)	Vector address	
27	USART	Transmission complete/transmit data register empty	-	-	Yes	Yes <sup>(1)</sup>	0x00 8074	
28	USART	Receive Register DATA FULL/overrun/idle line detected/parity error	-	-	Yes	Yes <sup>(1)</sup>	0x00 8078	
29	I2C	I2C interrupt <sup>(2)</sup>	Yes	Yes	Yes	Yes <sup>(1)</sup>	0x00 807C	

 Table 9. Interrupt mapping (continued)

1. In WFE mode, this interrupt is served if it has been previously enabled. After processing the interrupt, the processor goes back to WFE mode. Refer to Section *Wait for event (WFE) mode* in the RM0013 reference manual.

2. The device is woken up from Halt or Active-halt mode only when the address received matches the interface address.



	DATASIZE[7:0] Size of the data EEPROM area
	0x00: no data EEPROM area <sup>(1)</sup>
	0x01: 1 page reserved for data storage from 0x9FC0 to 0x9FFF <sup>(1)</sup>
OPT3	0x02: 2 pages reserved for data storage from 0x9F80 to 0x9FFF <sup>(1)</sup> <sup>(1)</sup>
0110	0x20: 32 pages reserved for data storage from 0x9800 to 0x9FFF <sup>(1)</sup>
	Refer to <i>Data EEPROM (DATA)</i> section in the STM8L reference manual (RM0013) for more details.
	DATASIZE[7:6] are forced to 0 internal by HW.
	IWDG_HW: Independent watchdog
	0: Independent watchdog activated by software
OPT4	1: Independent watchdog activated by hardware
0114	IWDG_HALT: Independent window watchdog reset on Halt/Active-halt
	0: Independent watchdog continues running in Halt/Active-halt mode
	1: Independent watchdog stopped in Halt/Active-halt mode
,	

### Table 11. Option byte description (continued)

1. 0x00 is the only allowed value for 4 Kbyte STM8L101xx devices.

**Caution:** After a device reset, read access to the program memory is not guaranteed if address 0x4807 is not programmed to 0x00.



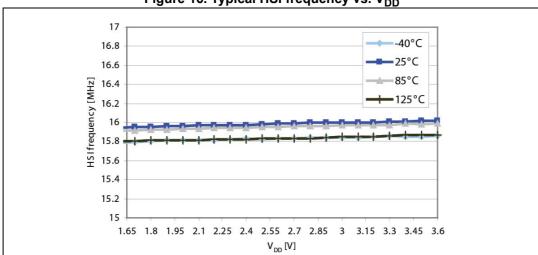
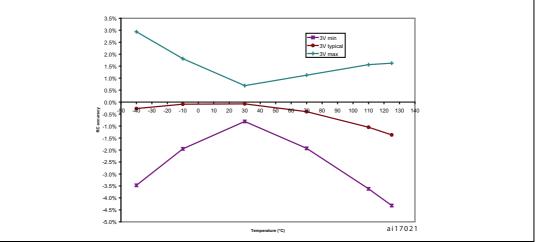
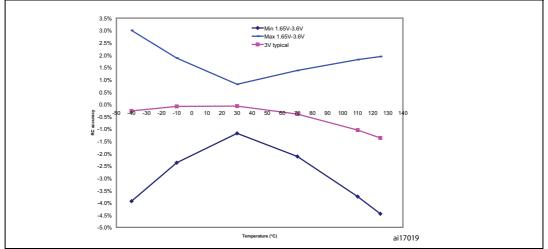


Figure 16. Typical HSI frequency vs. V<sub>DD</sub>









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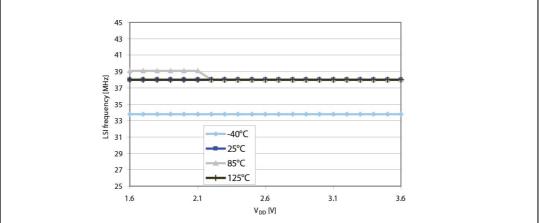
## Low speed internal RC oscillator (LSI)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>LSI</sub>	Frequency	-	26	38	56	kHz
f <sub>drift(LSI)</sub>	LSI oscillator frequency drift <sup>(2)</sup>	0 °C ≤T <sub>A</sub> ≤ 85 °C	-12	-	11	%

Table 23, LSI o	oscillator	characteristics	(1)
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1.  $V_{DD}$  = 1.65 V to 3.6 V, T<sub>A</sub> = -40 to 125 °C unless otherwise specified.

2. For each individual part, this value is the frequency drift from the initial measured frequency.



## Figure 19. Typical LSI RC frequency vs. $\mathrm{V}_{\mathrm{DD}}$

## 9.3.5 Memory characteristics

 $T_A$  = -40 to 125 °C unless otherwise specified.

#### Table 24. RAM and hardware registers

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>RM</sub>	Data retention mode <sup>(1)</sup>	Halt mode (or Reset)	1.4	-	-	V

1. Minimum supply voltage without losing data stored in RAM (in Halt mode or under Reset) or in hardware registers (only in Halt mode). Guaranteed by characterization, not tested in production.

#### Flash memory

Symbol	Parameter	Conditions	Min	Тур	Max (1)	Unit
V <sub>DD</sub>	Operating voltage (all modes, read/write/erase)	f <sub>MASTER</sub> = 16 MHz	1.65	-	3.6	V
+	Programming time for 1- or 64-byte (block) erase/write cycles (on programmed byte)	-	-	6	-	ms
Lprog	Programming time for 1- to 64-byte (block) write cycles (on erased byte)	-	-	3	-	ms

Table 25. Flash program memory



Symbol	Parameter	Conditions	Min	Тур	Max (1)	Unit
1	Programming/ erasing consumption	T <sub>A</sub> =+25 °C, V <sub>DD</sub> = 3.0 V	-	0.7	-	mA
Iprog		T <sub>A</sub> =+25 °C, V <sub>DD</sub> = 1.8 V	-	0.7	-	ШA
	Data retention (program memory) after 10k erase/write cycles at $T_A = +85$ °C	T <sub>RET</sub> = 55 °C	20 <sup>(1)</sup>	-	-	
t <sub>RET</sub>	Data retention (data memory) after 10k erase/write cycles at T <sub>A</sub> = +85 °C	T <sub>RET</sub> = 55 °C	20 <sup>(1)</sup>	-	-	years
	Data retention (data memory) after 300k erase/write cycles at $T_A = +125$ °C	T <sub>RET</sub> = 85 °C	1 <sup>(1)</sup>	-	-	
Ν	Erase/write cycles (program memory)	See notes <sup>(1)(2)</sup>	10 <sup>(1)</sup>	-	-	kovolca
N <sub>RW</sub>	Erase/write cycles (data memory)	See notes <sup>(1)(3)</sup>	300 <sup>(1)(4)</sup>	-	-	kcycles

Table 25.	Flash	program memory	(continued)
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1. Data based on characterization results, not tested in production.

2. Retention guaranteed after cycling is 10 years at 55 °C.

3. Retention guaranteed after cycling is 1 year at 55 °C.

4. Data based on characterization performed on the whole data memory (2 Kbytes).

# 9.3.6 I/O port pin characteristics

## **General characteristics**

Subject to general operating conditions for  $V_{DD}$  and  $T_A$  unless otherwise specified. All unused pins must be kept at a fixed voltage: using the output mode of the I/O for example or an external pull-up or pull-down resistor.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit	
V <sub>IL</sub>	Input low level voltage <sup>(2)</sup>	Standard I/Os	V <sub>SS</sub> -0.3	-	0.3 x V <sub>DD</sub>	V	
		True open drain I/Os	V <sub>SS</sub> -0.3	-	0.3 x V <sub>DD</sub>	v	
		Standard I/Os	0.70 x V <sub>DD</sub>	-	V <sub>DD</sub> +0.3		
V <sub>IH</sub>	Input high level voltage <sup>(2)</sup>	True open drain I/Os V <sub>DD</sub> < 2 V	0.70 x V <sub>DD</sub>		5.2	v	
		True open drain I/Os $V_{DD} \ge 2 V$	0.70 X V <sub>DD</sub>	-	5.5		
V <sub>hys</sub>	Schmitt trigger voltage hysteresis <sup>(3)</sup>	Standard I/Os	-	200	-	mV	
		True open drain I/Os	-	250	-		

Table 26. I/O static characteristics (1)	)
--	---



## **NRST** pin

The NRST pin input driver is CMOS. A permanent pull-up is present.  $R_{PU(NRST)}$  has the same value as  $R_{PU}$  (see *Table 26 on page 48*).

Subject to general operating conditions for  $V_{\text{DD}}$  and  $T_{\text{A}}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур <sup>(1)</sup>	Мах	Unit
V <sub>IL(NRST)</sub>	NRST input low level voltage <sup>(1)</sup>	-	$V_{SS}$	-	0.8	
V <sub>IH(NRST)</sub>	NRST input high level voltage <sup>(1)</sup>	-	1.4	-	V <sub>DD</sub>	V
V <sub>OL(NRST)</sub>	NRST output low level voltage	I <sub>OL</sub> = 2 mA	-	-	V <sub>DD</sub> -0.8	
R <sub>PU(NRST)</sub>	NRST pull-up equivalent resistor <sup>(2)</sup>	-	30	45	60	kΩ
V <sub>F(NRST)</sub>	NRST input filtered pulse <sup>(3)</sup>	-	-	-	50	ns
t <sub>OP(NRST)</sub>	NRST output pulse width	-	20	-	-	ns
V <sub>NF(NRST)</sub>	NRST input not filtered pulse <sup>(3)</sup>	-	300	-	_	ns

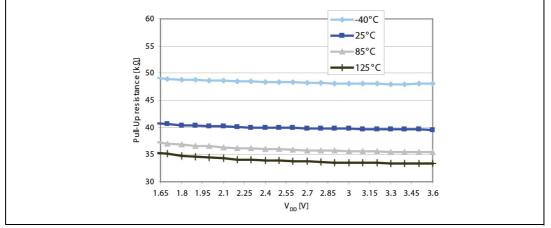
Table 30. NRST pin characteristics

1. Data based on characterization results, not tested in production.

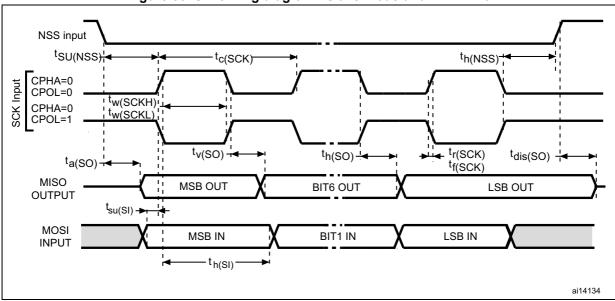
The R<sub>PU</sub> pull-up equivalent resistor is based on a resistive transistor (*Figure 30*). Corresponding I<sub>PU</sub> current characteristics are described in *Figure 31*.

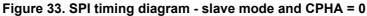
3. Data guaranteed by design, not tested in production.

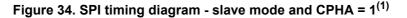


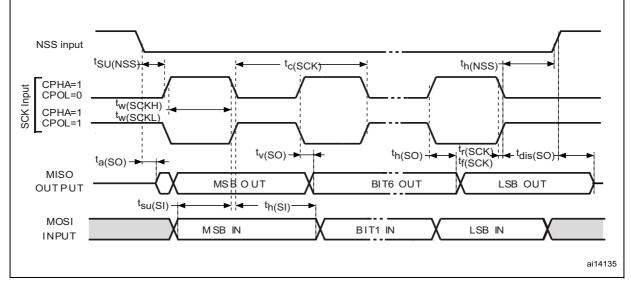












1. Measurement points are done at CMOS levels:  $0.3V_{\text{DD}}$  and  $0.7V_{\text{DD}}$ 



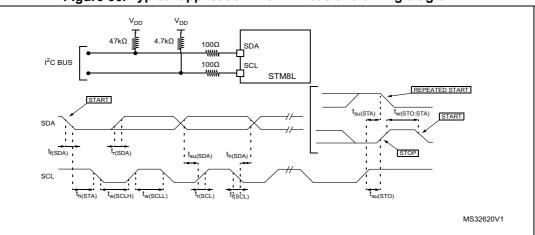


Figure 36. Typical application with I2C bus and timing diagram<sup>1)</sup>

1. Measurement points are done at CMOS levels: 0.3 x  $V_{\text{DD}}$  and 0.7 x  $V_{\text{DD}}$ 

#### 9.3.8 **Comparator characteristics**

Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Тур	Max <sup>(1)</sup>	Unit
V <sub>IN(COMP_REF)</sub>	Comparator external reference	-	-0.1	-	V <sub>DD</sub> -1.25	V
V <sub>IN</sub>	Comparator input voltage range	-	-0.25	-	V <sub>DD</sub> +0.25	V
V <sub>offset</sub> <sup>(2)</sup>	Comparator offset error	-	-	-	±20	mV
t <sub>START</sub>	Startup time (after BIAS_EN)	-	-	-	3 <sup>(1)</sup>	μs
	Analog comparator consumption	-	-	-	25 <sup>(1)</sup>	μA
I <sub>DD(COMP)</sub>	Analog comparator consumption during power-down	-	-	-	60 <sup>(1)</sup>	nA
t <sub>propag</sub> <sup>(2)</sup>	Comparator propagation delay	100-mV input step with 5-mV overdrive, input rise time = 1 ns	-	-	2 <sup>(1)</sup>	μs

Table 33. Comparator characteristics

1. Data guaranteed by design, not tested in production.

The comparator accuracy depends on the environment. In particular, the following cases may reduce the accuracy of the 2. comparator and must be avoided:

- Negative injection current on the I/Os close to the comparator inputs

Switching on I/Os close to the comparator inputs
Negative injection current on not used comparator input.
Switching with a high dV/dt on not used comparator input.
These phenomena are even more critical when a big external serial resistor is added on the inputs.



## 9.3.9 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

## Functional EMS (electromagnetic susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electromagnetic events until a failure occurs (indicated by the LEDs).

- **ESD**: Electrostatic discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 61000-4-2 standard.
- FTB: A burst of fast transient voltage (positive and negative) is applied to V<sub>DD</sub> and V<sub>SS</sub> through a 100 pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

## Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Prequalification trials:

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring. Refer to application note *Software techniques for improving microcontrollers EMC performance* (AN1015).

Symbol	Parameter	Conditions	Level/ Class
V <sub>FESD</sub>	Voltage limits to be applied on any I/O pin to induce a functional disturbance	LQFP32, V <sub>DD</sub> = 3.3 V	3B
	Fast transient voltage burst limits to be	LQFP32, V <sub>DD</sub> = 3.3 V, f <sub>HSI</sub>	3B
V <sub>EFTB</sub>	applied through 100 pF on $V_{DD}$ and $V_{SS}$ pins to induce a functional disturbance	LQFP32, V <sub>DD</sub> = 3.3 V, f <sub>HSI</sub> /2	4A

#### Table 34. EMS data



## Static latch-up

• LU: 2 complementary static tests are required on 10 parts to assess the latch-up performance. A supply overvoltage (applied to each power supply pin) and a current injection (applied to each input, output and configurable I/O pin) are performed on each sample. This test conforms to the EIA/JESD 78 IC latch-up standard. For more details, refer to the application note AN1181.

Tahlo	37	Floctrical	sensitivities
Iable	31.	Electrical	Selisitivities

Symbol	Parameter	Class
LU	Static latch-up class	II

# 9.4 Thermal characteristics

The maximum chip junction temperature  $(T_{Jmax})$  must never exceed the values given in *Table 16: General operating conditions on page 40.* 

The maximum chip-junction temperature,  $T_{Jmax}$ , in degrees Celsius, may be calculated using the following equation:

 $\mathsf{T}_{\mathsf{Jmax}} = \mathsf{T}_{\mathsf{Amax}} + (\mathsf{P}_{\mathsf{Dmax}} \times \Theta_{\mathsf{JA}})$ 

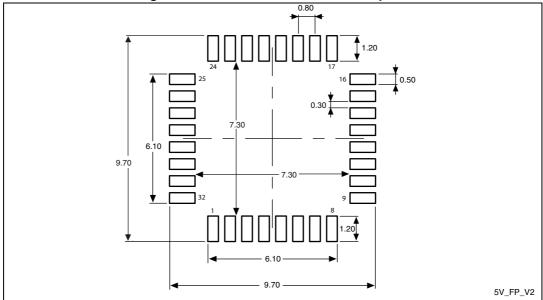
Where:

- T<sub>Amax</sub> is the maximum ambient temperature in °C
- $\Theta_{JA}$  is the package junction-to-ambient thermal resistance in ° C/W
- P<sub>Dmax</sub> is the sum of P<sub>INTmax</sub> and P<sub>I/Omax</sub> (P<sub>Dmax</sub> = P<sub>INTmax</sub> + P<sub>I/Omax</sub>)
- P<sub>INTmax</sub> is the product of I<sub>DD</sub> and V<sub>DD</sub>, expressed in watts. This is the maximum chip internal power.
- P<sub>I/Omax</sub> represents the maximum power dissipation on output pins where:

 $\mathsf{P}_{\mathsf{I}/\mathsf{Omax}} = \Sigma (\mathsf{V}_{\mathsf{OL}} * \mathsf{I}_{\mathsf{OL}}) + \Sigma ((\mathsf{V}_{\mathsf{DD}} - \mathsf{V}_{\mathsf{OH}}) * \mathsf{I}_{\mathsf{OH}}),$ 

taking into account the actual  $V_{OL}/I_{OL and} V_{OH}/I_{OH}$  of the I/Os at low and high level in the application.



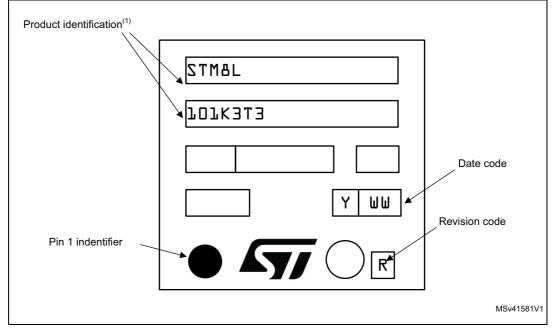


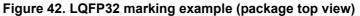
#### Figure 41. LQFP32 recommended footprint

1. Dimensions are expressed in millimeters.

## **Device marking**

The following figure gives an example of topside marking orientation versus pin 1 identifier location.



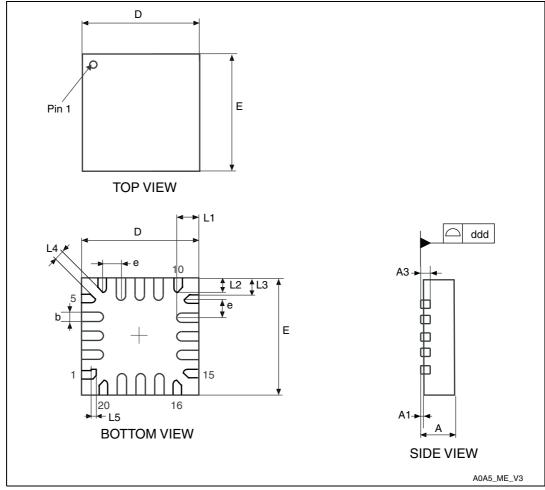


 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



# 10.4 UFQFPN20 package information

Figure 46. UFQFPN20 - 20-lead ultra thin fine pitch quad flat package outline (3x3 mm)



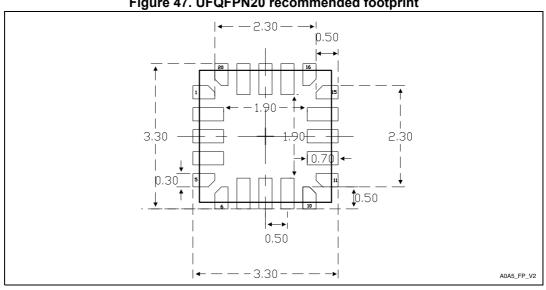
1. Drawing is not to scale.



Symbol		millimeters			inches <sup>(1)</sup>	
	Min	Тур	Мах	Min	Тур	Max
D	-	3.000	-	-	0.1181	-
E	-	3.000	-	-	0.1181	-
А	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
A3	-	0.152	-	-	0.0060	-
е	-	0.500	-	-	0.0197	-
L1	0.500	0.550	0.600	0.0197	0.0217	0.0236
L2	0.300	0.350	0.400	0.0118	0.0138	0.0157
L3	-	0.375	-	-	0.0148	-
L4	-	0.200	-	-	0.0079	-
L5	-	0.150	-	-	0.0059	-
b	0.180	0.250	0.300	0.0071	0.0098	0.0118
ddd	-	0.050	-	-	0.0020	-

## Table 42. UFQFPN20 - 20-lead ultra thin fine pitch quad flat package (3 x 3 mm) mechanical data

1. Values in inches are rounded to 4 decimal digits



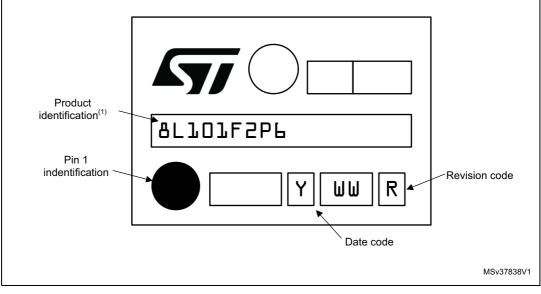
## Figure 47. UFQFPN20 recommended footprint

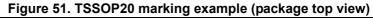
1. Dimensions are in millimeters.



## **Device marking**

The following figure gives an example of topside marking orientation versus pin 1 identifier location.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



# 12.2 Software tools

STM8 development tools are supported by a complete, free software package from STMicroelectronics that includes ST Visual Develop (STVD) IDE and the ST Visual Programmer (STVP) software interface. STVD provides seamless integration of the Cosmic and Raisonance C compilers for STM8. A free version that outputs up to 32 Kbytes of code is available.

## 12.2.1 STM8 toolset

**STM8** toolset with STVD integrated development environment and STVP programming software is available for free download at *www.st.com*. This package includes:

ST Visual Develop - Full-featured integrated development environment from ST, featuring

- Seamless integration of C and ASM toolsets
- Full-featured debugger
- Project management
- Syntax highlighting editor
- Integrated programming interface
- Support of advanced emulation features for STice such as code profiling and coverage

**ST Visual Programmer (STVP)** – Easy-to-use, unlimited graphical interface allowing read, write and verify of the STM8 microcontroller Flash program memory, data EEPROM and option bytes. STVP also offers project mode for saving programming configurations and automating programming sequences.

## 12.2.2 C and assembly toolchains

Control of C and assembly toolchains is seamlessly integrated into the STVD integrated development environment, making it possible to configure and control the building of user application directly from an easy-to-use graphical interface.

Available toolchains include:

- Cosmic C compiler for STM8 One free version that outputs up to 32 Kbytes of code is available. For more information, see www.cosmic-software.com.
- Raisonance C compiler for STM8 One free version that outputs up to 32 Kbytes of code. For more information, see www.raisonance.com.
- **STM8 assembler linker** Free assembly toolchain included in the STVD toolset, which allows the user to assemble and link their application source code.

# 12.3 Programming tools

During the development cycle, STice provides in-circuit programming of the STM8 Flash microcontroller on the user's application board via the SWIM protocol. Additional tools are to include a low-cost in-circuit programmer as well as ST socket boards, which provide dedicated programming platforms with sockets for programming the STM8.

For production environments, programmers will include a complete range of gang and automated programming solutions from third-party tool developers already supplying programmers for the STM8 family.



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DocID15275 Rev 15

